

*Nuclear Physics
and Atomic Energy*



Quality Assurance of the Microstrip Detectors for CBM Silicon Tracker Station. Tests at KINR.

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**Ukrainian-German Workshop
“Cooperation in the Framework of FAIR Project”
Kharkiv, Ukraine, 26th September 2014.**

KINR at the CBM Collaboration.

CBM – experiment (FAIR)

High Energy Physics Department

Kiev Institute for Nuclear Research NASU (KINR)

CBM Team of KINR:

M. Borysova, A. Kovalchuk, V. Kyva, V. Militsija, I. Panasenko, V. Pugatch, D. Storozhyk, A. Lymanets (KINR & Tübingen, Physikalisches Institut, Eberhard Karls Universität Tübingen), A. Malygina (KINR & Frankfurt, Institut für Kernphysik, Goethe Universität Frankfurt), I. Sorokin (KINR & GSI, Darmstadt)

STS TDR.

KINR group planned contribution.

STS development and prototyping (year 2014 + ...)

- Testing of sensors – (in collaboration with GSI, CIS)
 - Sensor prototype with STS-XYTER FEE (in collaboration with GSI)
 - Sensor prototype with STS-XYTER FEE and tap bonded flat cables (in collaboration with GSI)
- Integration of components into ladder prototype (in collaboration with GSI, Tübingen, KINR)
 - Test Ladder prototype (in collaboration with GSI)
- **For carrying out this work KINR team has built the laser and radioactive sources test stand equipped with the whole readout chain based on the STS-XYTER FEE.**

Later stages of the CBM Construction (2015 -2016) KINR team plans.

- **Production, Assembly and System Integration**
- **STS Modules pre-production as well as production (in collaboration with GSI, Tübingen, JINR)**
- **STS Ladders production (in collaboration with GSI, Tübingen, JINR).**

Currently this is planned to be performed on the basis of participation of the KINR team members in construction work at GSI, Tübingen.

We plan to apply for grants from the Ministry of Science and Education and State Agency on Science ... (?) of Ukraine for building a necessary infrastructure at KINR.

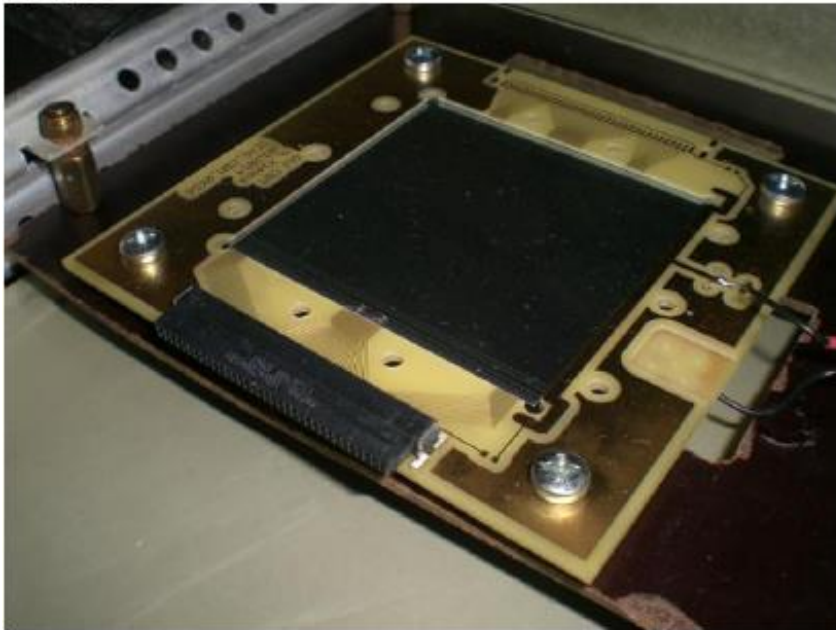
Characterization of prototype sensors for the CBM Silicon Tracking System.

Year 2014. (Examples of Results).

Full size CBM-05

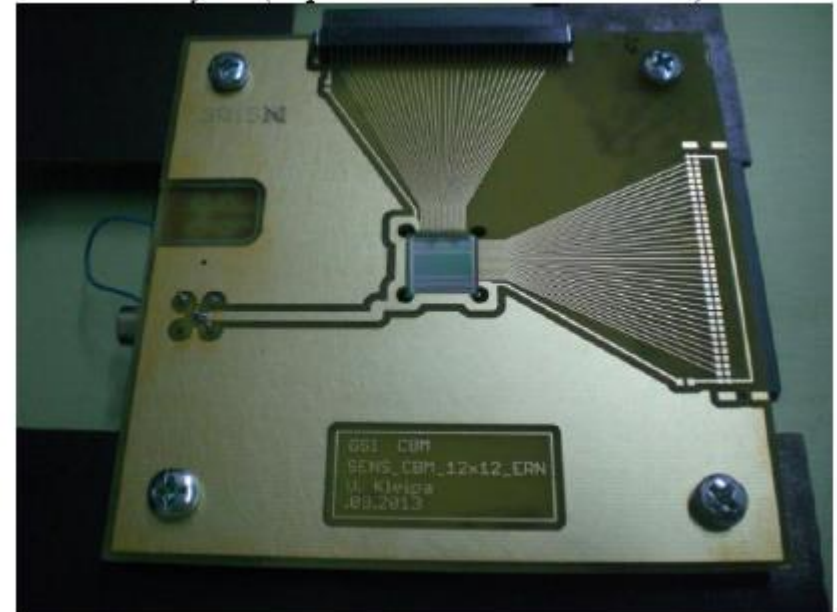
(transferred to Kiev from Kharkiv, June 2014)

CBM05



Three Baby-CBM-05 sensors (from GSI – June 2014)

CBM05-baby #1 (опромінений великою дозою)

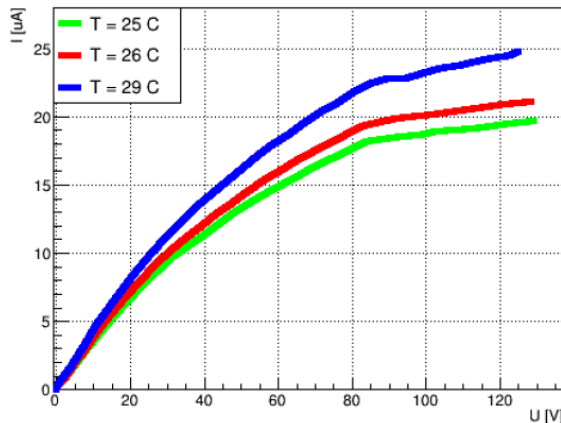


Two sensors were irradiated at the KINR isochronous cyclotron:
Alpha – particles – 86 MeV.

IV - measurements

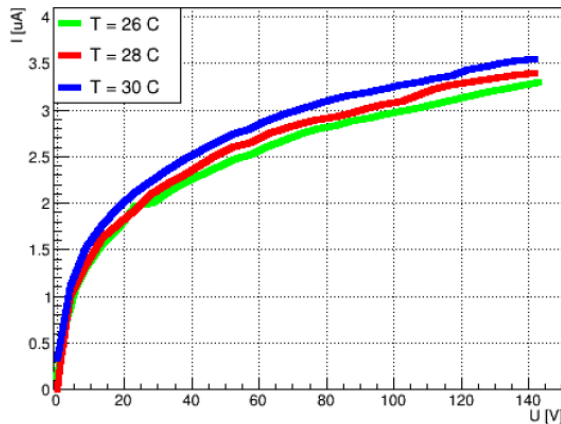
IV. Non-irradiated sensors

IV-curves for CBM05 full-size sensor



**Full-size
CBM-05**

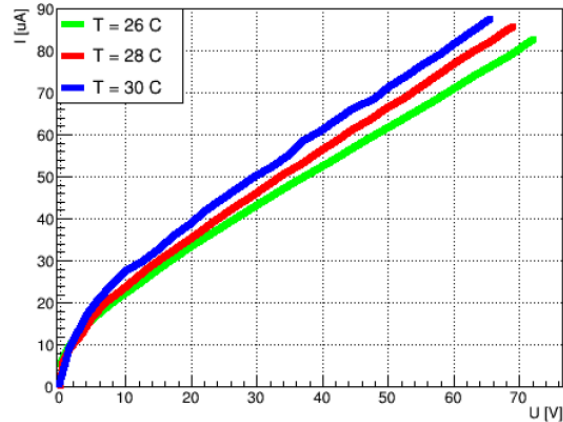
IV-curves for CBM05 baby sensor



**Baby-
sensor**

IV. Irradiated sensors.

IV-curves for CBM05 irradiated baby sensor #1



Fluence:

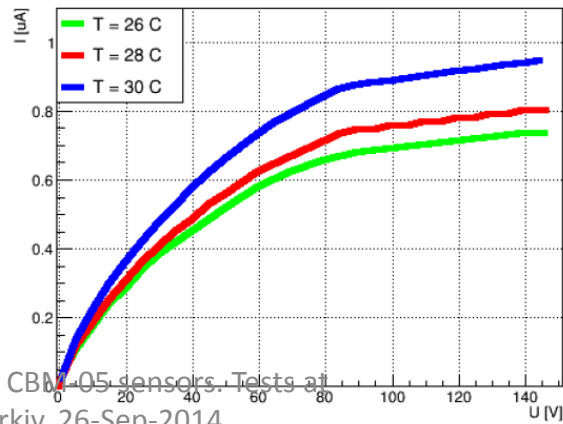
$$1.1 \times 10^{14} n_{eq} / cm^2$$

FDV (?) = >150 V



Alpha-particles – 86 MeV.

IV-curves for CBM05 irradiated baby sensor #2



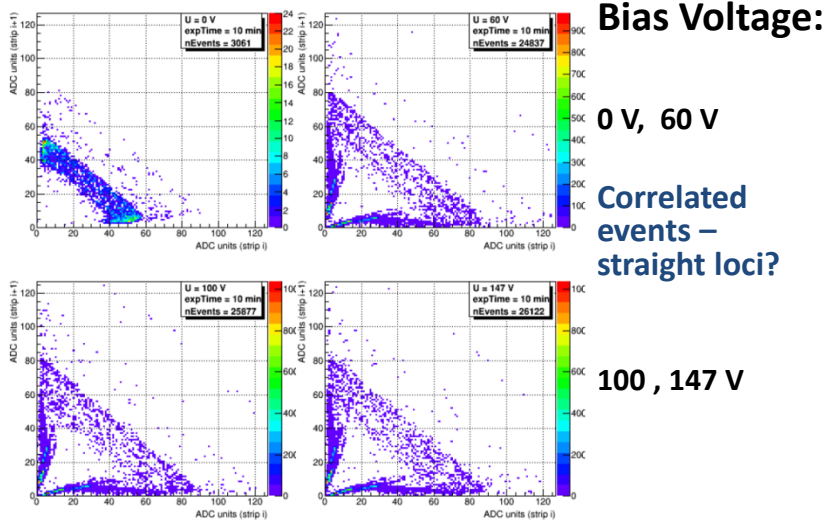
Fluence:

$$1.2 \times 10^{13} n_{eq} / cm^2$$

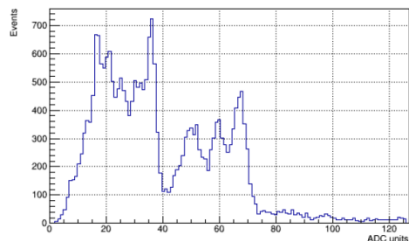
FDV = 25 V

Studies with ^{239}Pu α – source (coincident two-dimensional spectra at different bias voltages)

Baby – sensor (non-irradiated)
data from p-side (α – source from p-side)

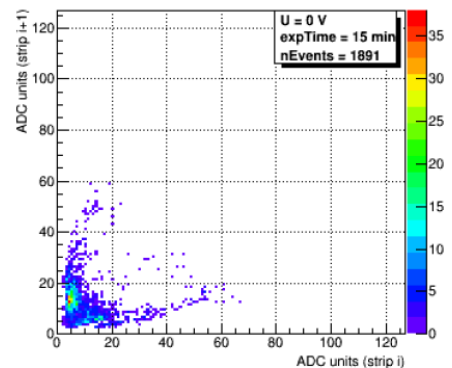


І проєкція амплітудного розподілу з міжстріпового проміжку при 147 В дає три альфа-лінії:



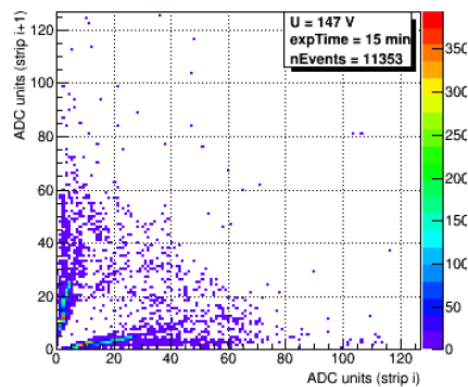
Single dimensional spectrum – projection over the diagonal

Baby – sensor (irradiated)
data from p-side (α – source from p-side)



Bias Voltage:

0 V,



147 V

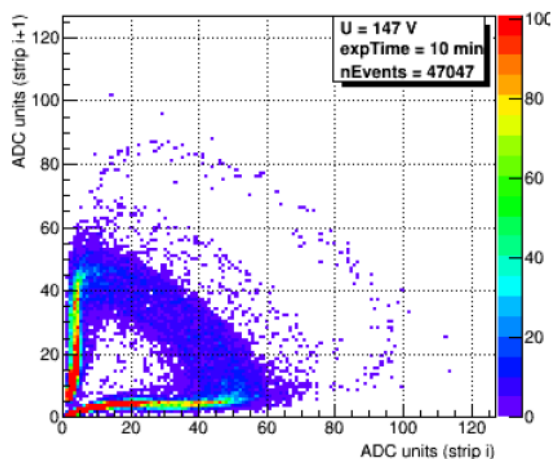
No clear Lines from ^{239}Pu α – source

Negative pulses ?

Correlated events – straight loci?

Studies with ^{239}Pu α – source (coincident two-dimensional spectra at different bias voltages)

Baby – sensor (non-irradiated)
data from n-side (α – source from p-side)



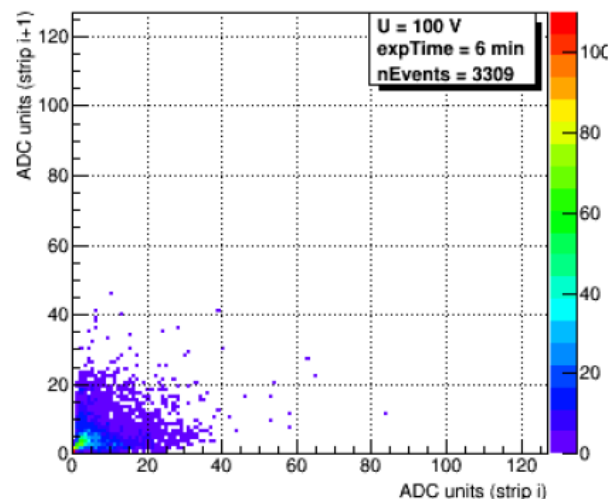
Bias
Voltage:

147 V

Data appear
already at 10 V

Correlated
signals-
straight loci ?

Baby – sensor (irradiated)
data from n-side (α – source from p-side)



Bias
Voltage:

100 V

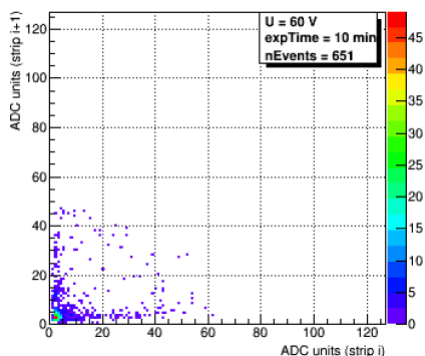
High noise

Full
depletion
was not
reached

Studies with ^{239}Pu α – source (coincident two-dimensional spectra at different bias voltages)

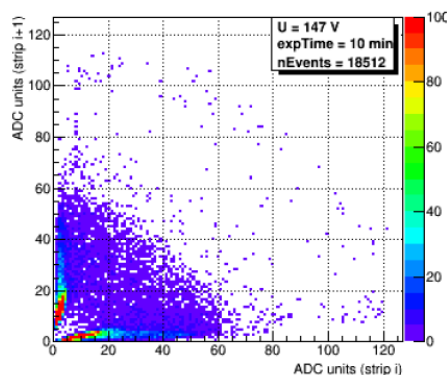
Baby – sensor (**non-irradiated**)
data from p-side (α – source from n-side)

Baby – sensor (**irradiated**)
data from p-side (α – source from n-side)

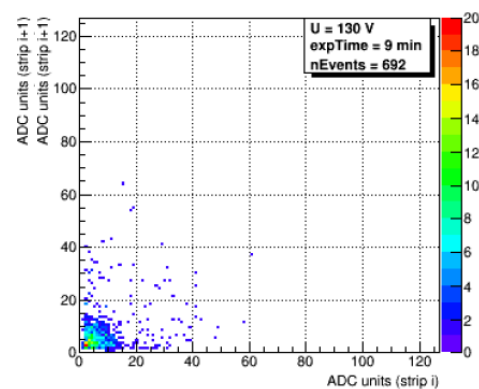


Bias Voltage:

Data appear at
60 V



147 V
**Correlated signals-
straight loci**
?



Bias Voltage:

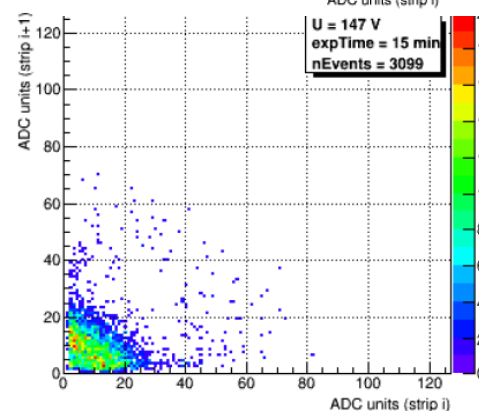
(data appear at
115 V)

130 V,



147 V

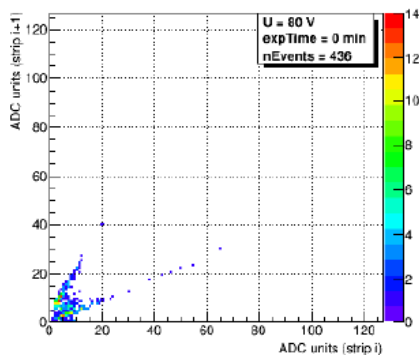
**Much less events
from ^{239}Pu
 α – source**



Studies with ^{239}Pu α – source

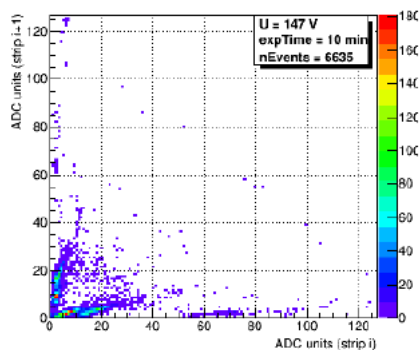
(coincident two-dimensional spectra at different bias voltages)

Baby – sensor (non-irradiated)
data from n-side (α – source from n-side)



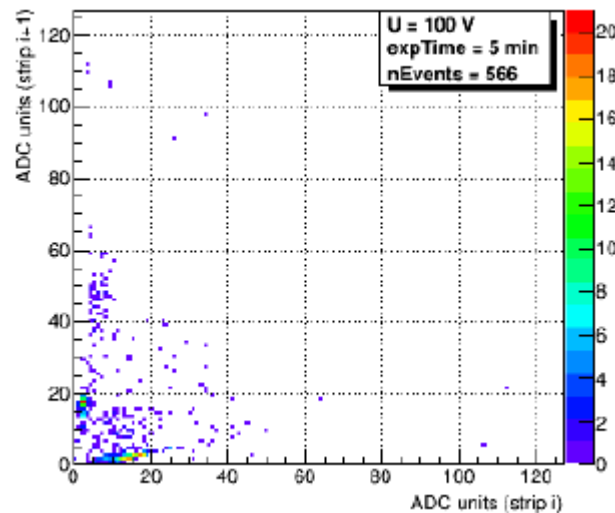
Bias
Voltage:
80 V

Data appear
at 50 V



147 V
Correlated
signals-
straight loci
?

Baby – sensor (irradiated)
data from n-side (α – source from n-side)



Bias
Voltage:

100 V,

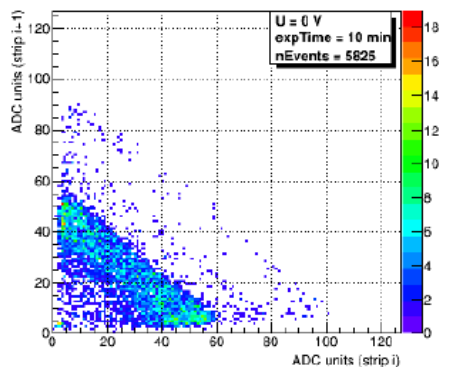


Much less
events
from ^{239}Pu
 α – source

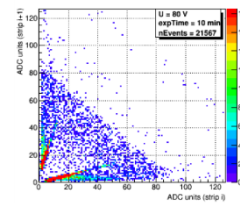
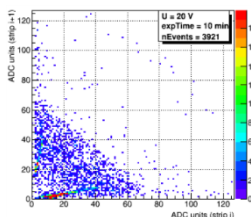
Negative
pulses ?

Studies with ^{239}Pu α – source (coincident two-dimensional spectra at different bias voltages)

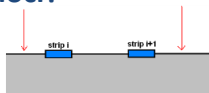
Full size – sensor (non-irradiated)
data from p-side (α – source from p-side)



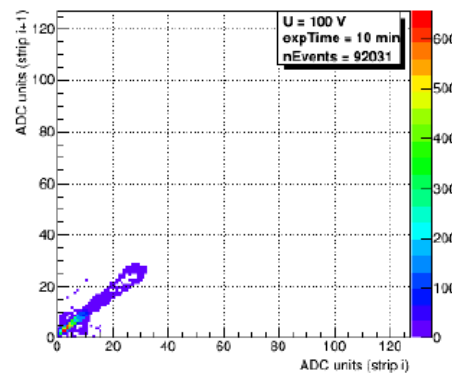
Bias Voltage:
0 V



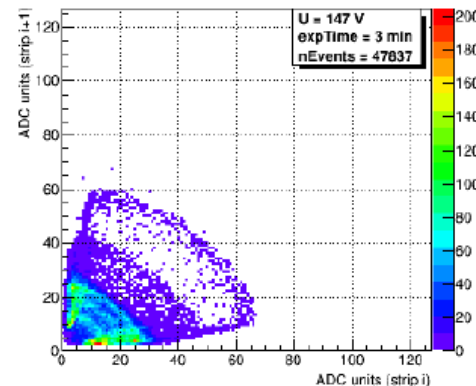
147 V
Poor resolution – no peaks from ^{239}Pu α – source
Correlated events – straight loci?



Full size – sensor (non-irradiated)
data from n-side (α – source from p-side)



Bias Voltage:
100 V,

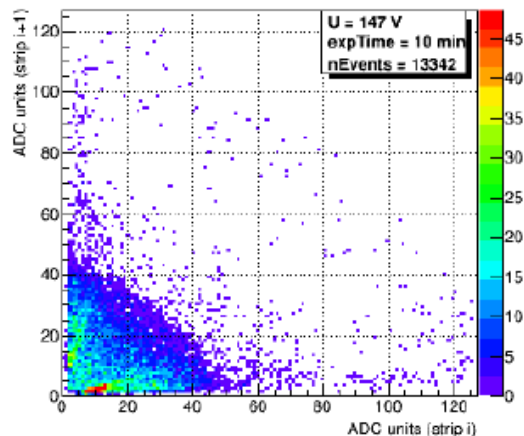


147 V
Lines from ^{239}Pu α – source are pronounced

The population of the straight loci grows up as the bias voltage increases.

Studies with ^{239}Pu α – source (coincident two-dimensional spectra at different bias voltages)

Full size – sensor (non-irradiated)
data from p-side (α – source from n-side)



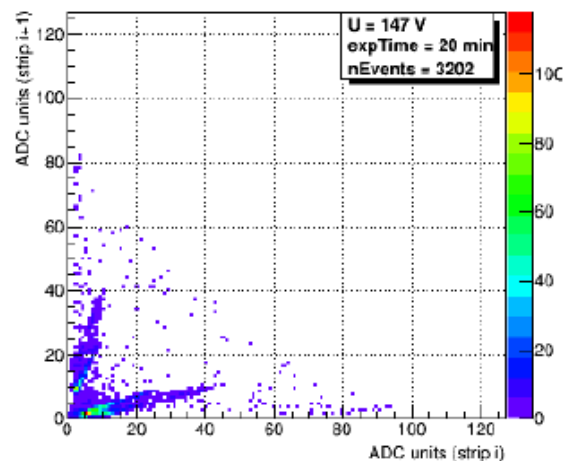
Bias
Voltage:

147 V,

Correlated
events –
straight
loci?

no peaks
from ^{239}Pu
 α – source

Full size – sensor
data from n-side (α – source from p-side)



Bias
Voltage:

147 V

Correlated
events –
straight
loci?

Brief Summary

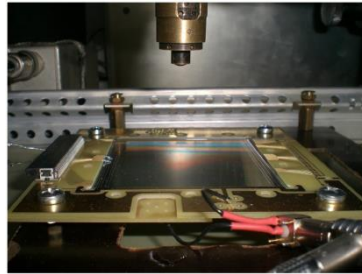
on peculiarities of the alpha-tests data

- All 4 tested sensors exhibit appearance of negative pulses (instead of expected positive ones) being irradiated from p-side as well as from n-side:
 - p-side – negative pulses go down as the biasing voltage increases
 - n-side – both polarities pulses are present
- Smearing of the response to alphas indicated existence/appearance of the dead layer at both surfaces of sensors

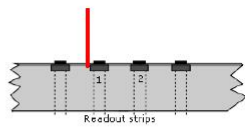
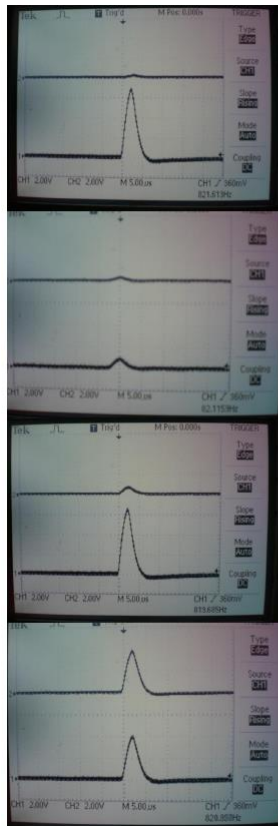
Studies with Laser stand (640 nm)

(coincident two-dimensional spectra at different bias voltages)

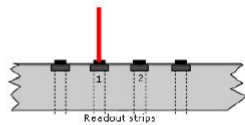
Full size – sensor data from p-side



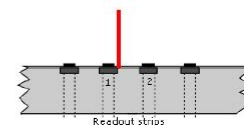
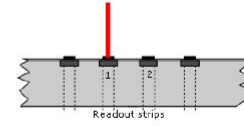
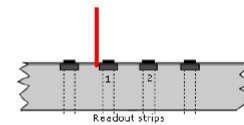
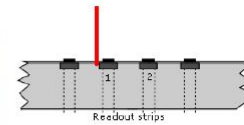
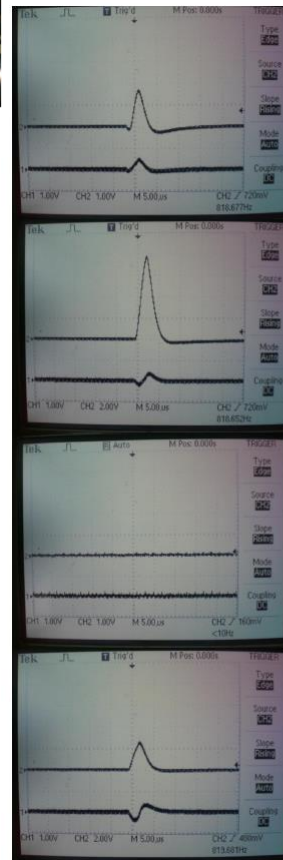
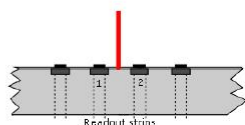
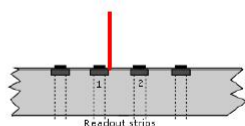
Full size – sensor data from p-side



Bias Voltage:



0 V



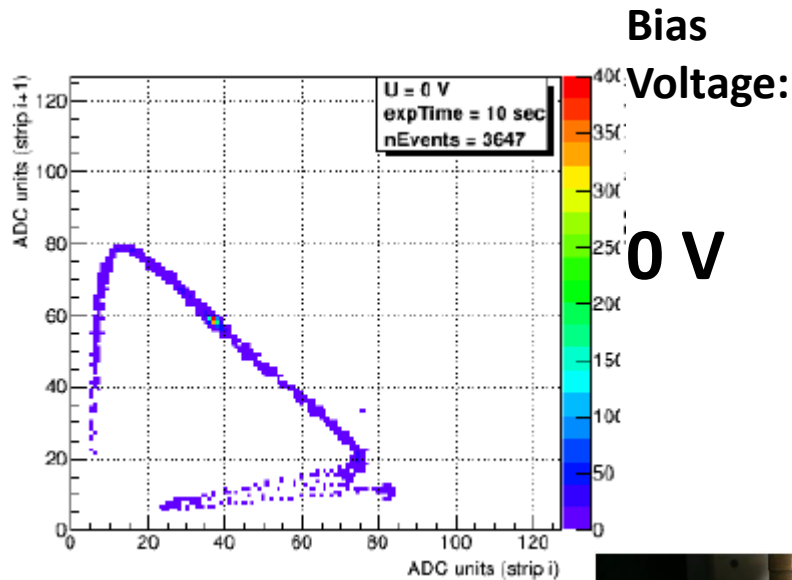
Bias Voltage:

147 V

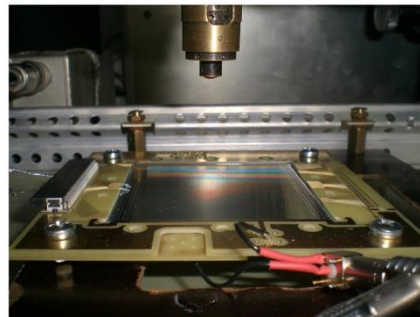
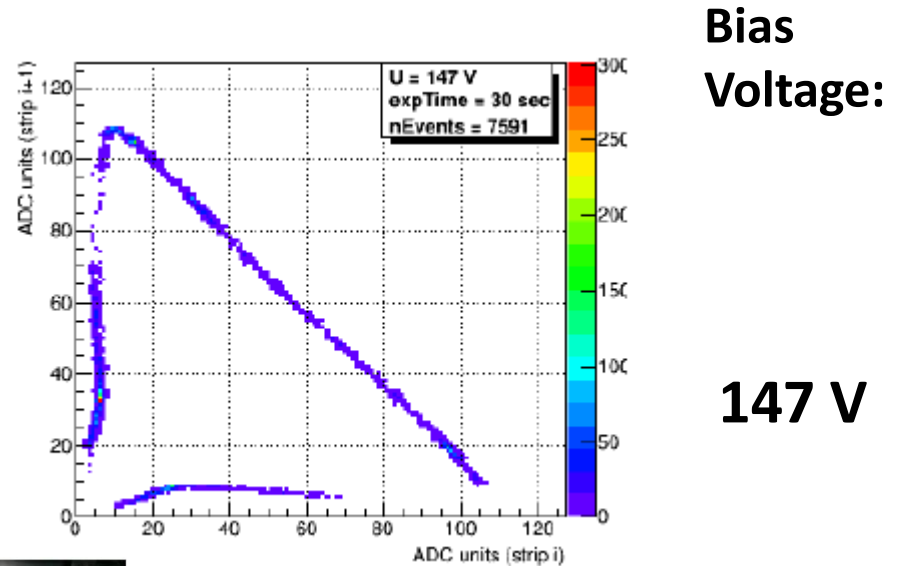
Studies with Laser stand (640 nm)

(coincident two-dimensional spectra at different bias voltages)

Full size – sensor
data from p-side



Full size – sensor
data from p-side



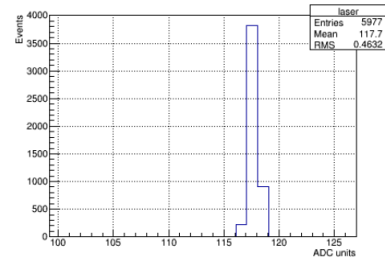
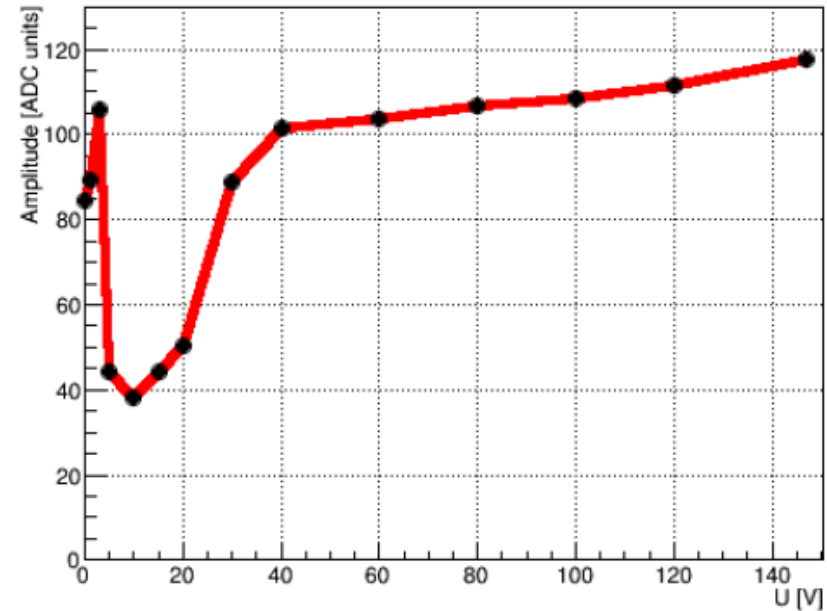
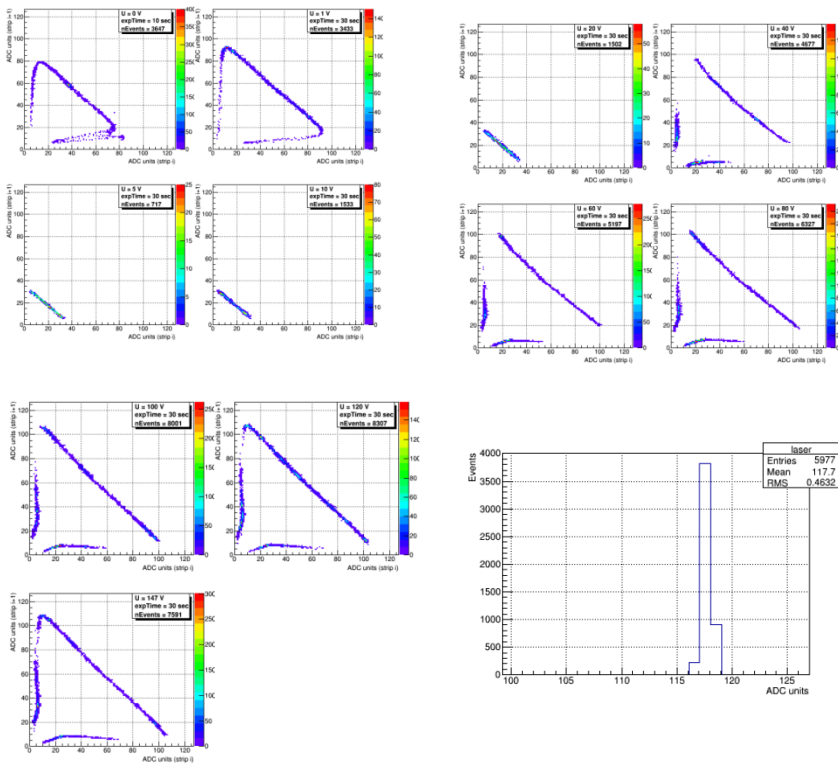
The sum of amplitudes
'Left+Right' strips grows up with the
biasing voltage increase.

Yet! See the next slide 'peculiarity'

Studies with Laser stand (640 nm) (coincident two-dimensional spectra at different bias voltages)

Full size – sensor data from p-side.
Biasing voltage increases for 0 to 147 V.

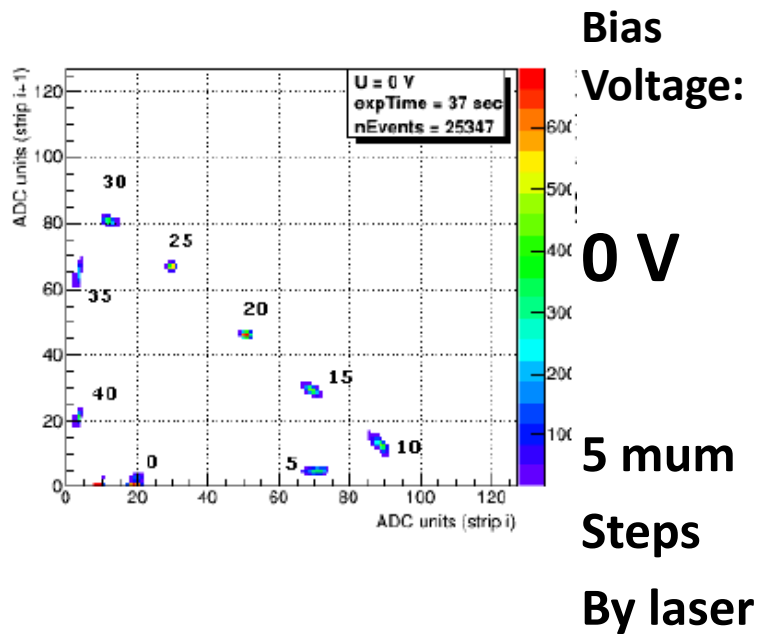
Full size – sensor data from p-side.
Biasing voltage increases for 0 to 147 V.



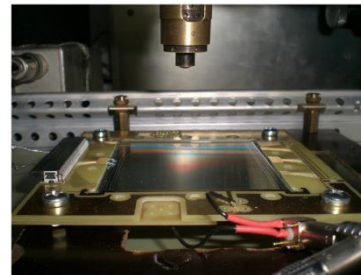
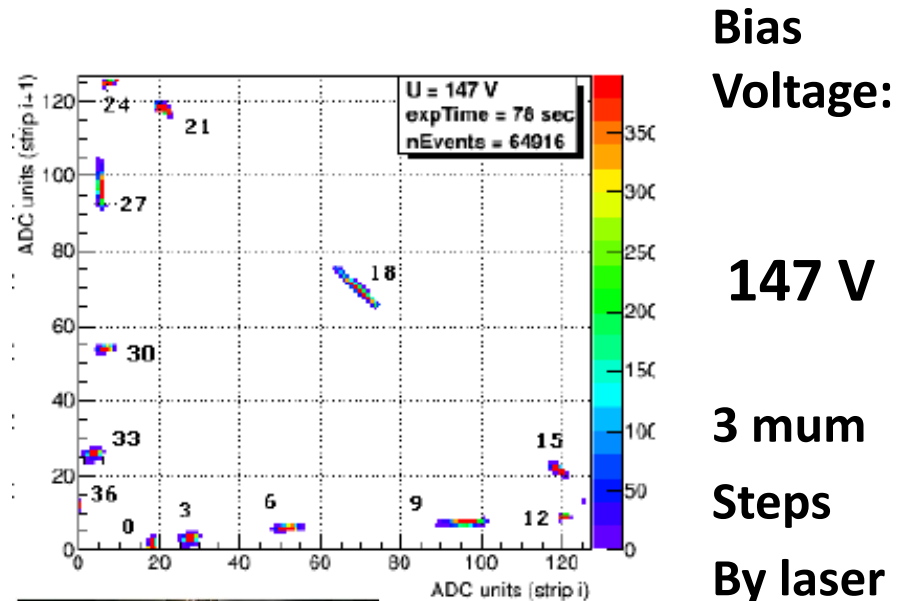
Studies with Laser stand (640 nm)

(coincident two-dimensional spectra at different bias voltages)

Full size – sensor
data from p-side

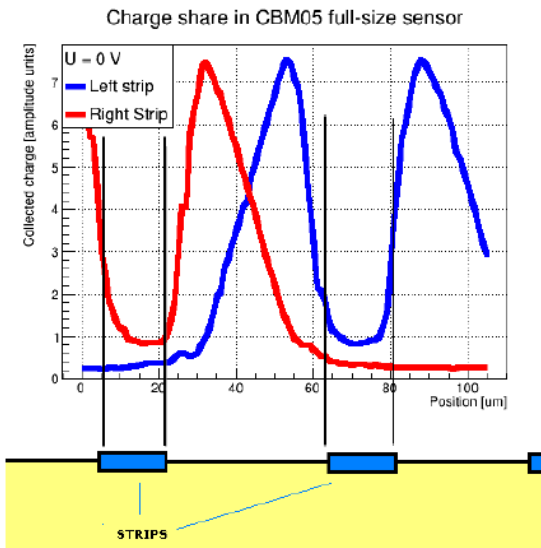


Full size – sensor
data from p-side



Studies with Laser stand (640 nm) (coincident two-dimensional spectra at different bias voltages)

Full size – sensor
data from p-side

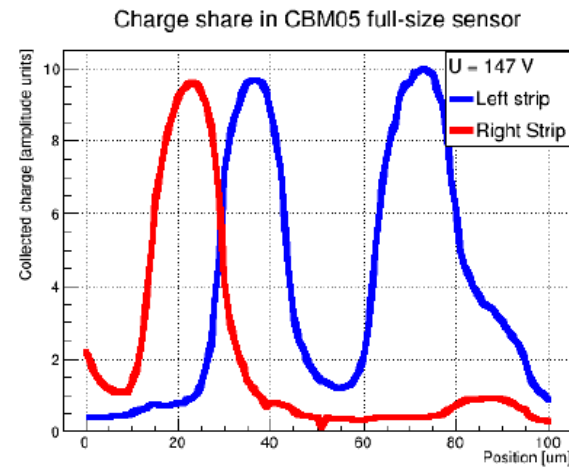


Bias
Voltage:

0 V

5 mm
Steps
By laser

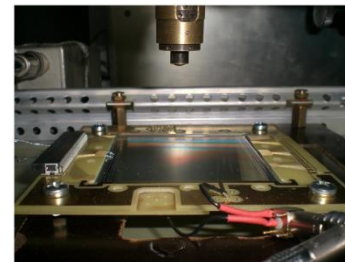
Full size – sensor
data from p-side



Bias
Voltage:

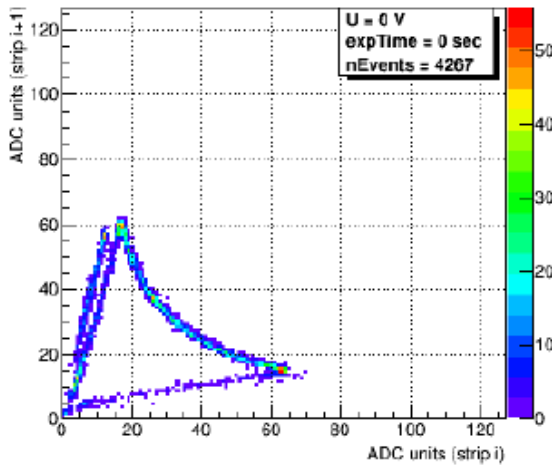
147 V

3 mm
Steps
By laser



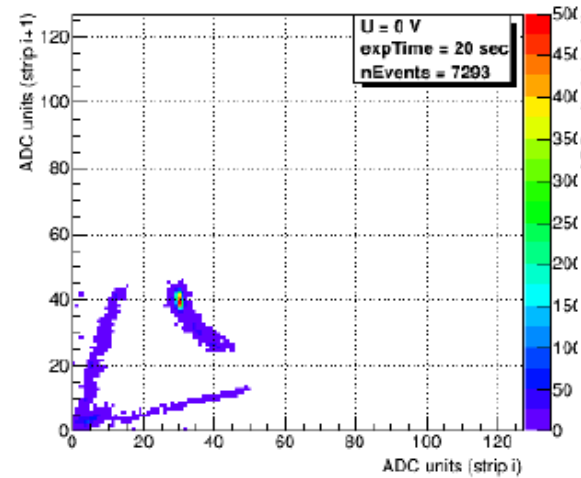
Studies with Laser stand (640 nm) (coincident two-dimensional spectra at different bias voltages)

Baby– sensor (non-irradiated)
data from p-side

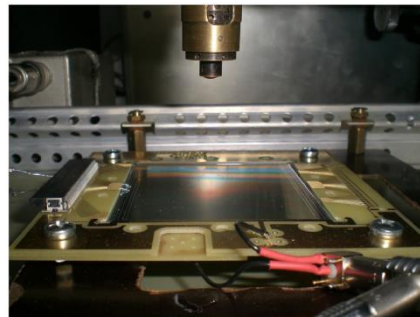


Bias
Voltage:
0 V

Baby– sensor (irradiated)
data from p-side



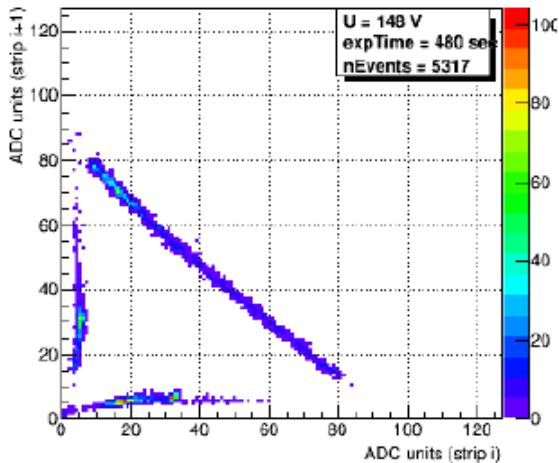
Bias
Voltage:
0 V



Studies with Laser stand (640 nm)

(coincident two-dimensional spectra at different bias voltages)

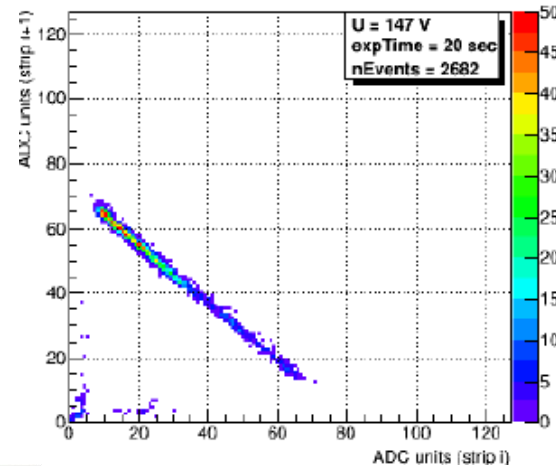
Baby– sensor (non- irradiated)
data from p-side



Bias
Voltage:

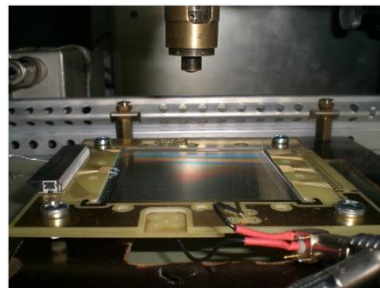
147 V

Baby– sensor (irradiated)
data from p-side



Bias
Voltage:

147 V



Charge collected
went down
by ~ 25 %.

Summary and outlook

1. Quality assurance setups at KINR (alphas as well as laser) for Silicon Microstrip Sensors are in operation.
2. 2 sensors irradiated at KINR isochronous cyclotron and two non-irradiated sensors were characterized.
3. All 4 sensors tested by alphas as well as by laser demonstrated nearly expected performance wrt to charge sharing in the interstrip gap.
4. Very good position resolution !
5. YET ... To be further studied/understood:
 - appearance of the correlated events – ‘straight loci’ in two-dimensional distribution of the charge collected at adjacent strips (pick-up ?).
 - opposite polarity pulses at adjacent strips?
 - dead layers (10-20 μm) at the p-n-sides - ?
6. Next steps:
 - MIP – studies
 - New sensors

This work is ongoing and is partially funded via the NASU budget. On the time to time basis there are related business trips to GSI, supported by the CBM.

We plan to apply for financial support (including payment of fee) from the Ministry of Science and Education and State Agency on Science (?) of Ukraine.

Thank you for your attention !